IN THE CLAIMS:

Please cancel claims 9-11 and 13-19.

Please add new claims 20-22:

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20. A method of fabricating a polysilicon film, comprising the steps of:

providing a substrate;

depositing an amorphous silicon film on the substrate by the process of physical vapor deposition;

depositing a metal catalyst film on the amorphous silicon film; and

annealing the amorphous silicon film and the metal catalyst film to form a crystallized silicon film by pure metal induced crystallization, wherein the annealing step is conducted at a temperature greater than 650 °C and for a time period greater than 200 seconds and less than 800 seconds.

21. The method of claim 1 wherein said metal catalyst is chosen from the group consisting of aluminum, indium tin oxide, nickel, cobalt, palladium and germanium.

22. A method of fabricating a polysilicon film, comprising the steps of:

a' amd'd.

providing a substrate;

depositing an amorphous silicon film on the substrate by the process of physical vapor deposition;

after deposition of said amorphous silicon film, depositing a metal catalyst film on selected regions of the amorphous silicon film; and

annealing the amorphous silicon film and the metal catalyst film to form a crystallized silicon film by pure metal induced crystallization in said selected regions.